

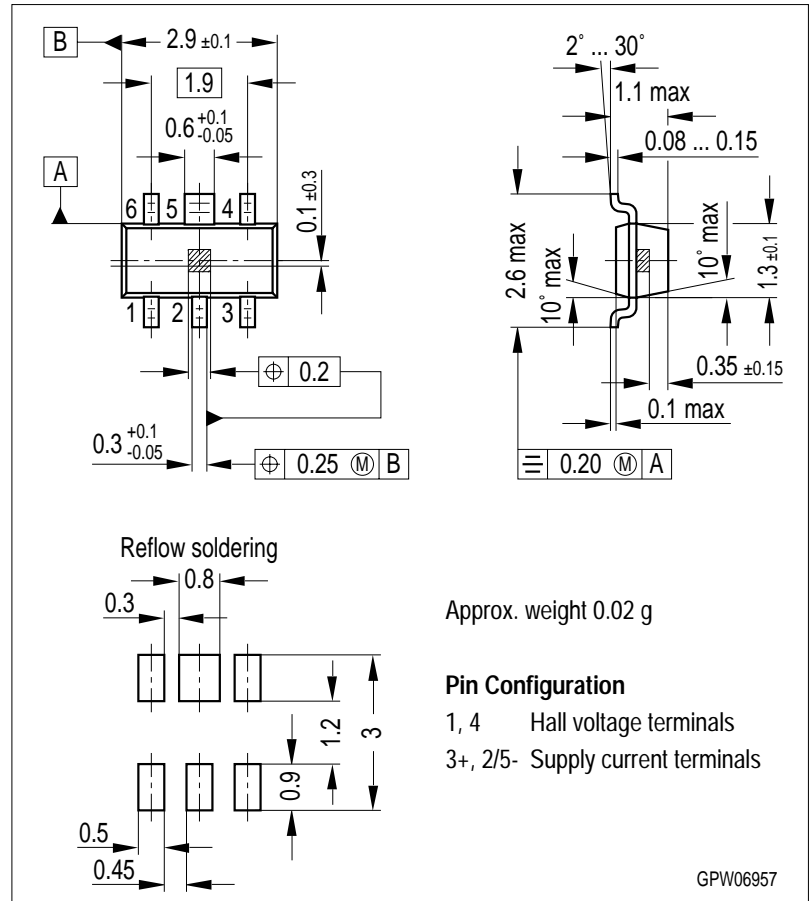
## Version 2.0

### Features

- Hall sensor on Cu-leadframe for SMT-technology, MW-6 package
- High sensitivity
- High temperature range
- Small linearity error
- Low offset voltage
- Low TC of sensitivity resistances
- This Hall sensor combines the advantages of non-magnetic leadframe and SMT capability

### Typical Applications

- Rotation and position sensing
- Current and power measurement
- Magnetic field measurement
- Control of brushless DC motors



Dimensions in mm

| Type   | Marking | Ordering Code |
|--------|---------|---------------|
| KSY 16 | s16     | Q62705-K338   |

The KSY 16 is an ion-implanted Hall sensor in a monocrystalline GaAs-material, built into an SMT package (MW-6). It is outstanding for a high magnetic sensitivity and low temperature coefficients. The 0.35 × 0.35 mm<sup>2</sup> chip is mounted onto a non-magnetic leadframe. The active area is placed approx. 0.45 mm below the surface of the package.

### Absolute Maximum Ratings

| Parameter                          | Symbol    | Limit Values | Unit |
|------------------------------------|-----------|--------------|------|
| Operating temperature              | $T_A$     | - 40...+ 150 | °C   |
| Storage temperature                | $T_{stg}$ | - 50...+ 160 | °C   |
| Supply current                     | $I_1$     | 7            | mA   |
| Thermal conductivity <sup>1)</sup> | $G_{thC}$ | $\geq 2.2$   | mW/K |

### Electrical Characteristics ( $T_A = 25\text{ °C}$ )

|  |                   |                                  |          |
|--|-------------------|----------------------------------|----------|
| Nominal supply current   | $I_{1N}$          | 5                                | mA       |
| Open-circuit sensitivity   | $K_{B0}$          | 190...260                        | V/AT     |
| Open-circuit Hall voltage<br>$I = I_{1N}, B = 0.1\text{ T}$                                  | $V_{20}$          | 95...130                         | mV       |
| Ohmic offset voltage<br>$I = I_{1N}, B = 0\text{ T}$   | $V_{R20}$         | $\leq \pm 20$                    | mV       |
| Linearity of Hall voltage<br>$B = 0...0.5\text{ T}$<br>$B = 0...1\text{ T}$                  | $F_L$<br>$F_L$    | $\leq \pm 0.2$<br>$\leq \pm 0.7$ | %<br>%   |
| Input resistance $B = 0\text{ T}$  | $R_{10}$          | 900...1200                       | $\Omega$ |
| Output resistance $B = 0\text{ T}$   | $R_{20}$          | 900...1200                       | $\Omega$ |
| Temperature coefficient of the open-circuit Hall voltage<br>$I_1 = I_{1N}, B = 0.1\text{ T}$ | $TC_{V20}$        | $\sim - 0.03...- 0.07$           | %/K      |
| Temperature coefficient of the internal resistance<br>$B = 0\text{ T}$                       | $TC_{R10, R20}$   | $\sim 0.1...0.18$                | %/K      |
| Change of offset voltage within the temperature range <sup>2)</sup>                          | $ \Delta V_{R0} $ | $\leq 2$                         | mV       |

### Connection of a Hall Sensor with a Power Source

Since the voltage on the component must not exceed 10 V, the connection to the constant current supply should only be done via a short circuit by-pass. The by-pass circuit-breaker shall not be opened before turning on the power source. This is to avoid damage to the Hall sensor due to power peaks.

<sup>1)</sup> Thermal conductivity chip-ambient when mounted on alumina ceramic 15 mm × 17 mm × 0.7 mm

<sup>2)</sup> AQL: 0.65